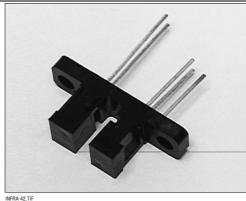
HOA2003

Transmissive Optoschmitt Sensor

FEATURES

- Direct TTL interface
- Buffer logic
- 0.010 in.(2.54 mm) offset detector leads
- 0.125 in.(3.18 mm) slot width
- Accurate position sensing
- · Dust protective housing



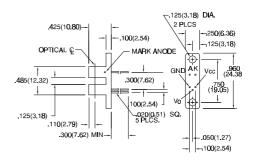
DESCRIPTION

The HOA2003 consists of an infrared emitting diode facing an Optoschmitt detector encased in a black thermoplastic housing. The photodetector consists of a photodiode, amplifier, voltage regulator, Schmitt trigger and an NPN output transistor with 10 $\mbox{k}\Omega$ (nominal) pullup resistor. The buffer logic provides a high output when the optical path is clear, and a low output when the path is interrupted. The HOA2003 utilizes an IR transmissive polysulfone housing which features smooth optical faces without external aperture openings; this feature is desirable when aperture blockage from airborne contaminants is a possibility. The detector has a 0.010 in.(.254 mm) x 0.040 in.(1.02 mm) vertical aperture which is ideal for use in applications in which maximum position resolution is desired. The HOA2003 employs plastic molded components. For additional component information see SEP8506 and SDP8600.

Housing material is polysulfone. Housings are soluble in chlorinated hydrocarbons and ketones. Recommended cleaning agents are methanol and isopropanol.

OUTLINE DIMENSIONS in inches (mm)

3 plc decimals ±0.010(0.25) 2 plc decimals ±0.020(0.51)



DIM_064.ds4



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ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
IR EMITTER						
Forward Voltage	VF			1.6	V	I _F =20 mA
Reverse Leakage Current	I _R			10	μΑ	V _R =3 V
DETECTOR						
Operating Supply Voltage	Vcc	4.5		10	V	
Low Level Supply Current	Iccl	4.0		12	mA	Vcc=5 V
Low Level Supply Current		5.0		15		V _{CC} =12 V
High Level Supply Current	Іссн	2.0		10	mA	Vcc=5 V
High Level Supply Current		3.0		12		Vcc=12 V
Low Level Output Voltage	Vol			0.4	V	I _{OL} =12.8 mA, I _F =0 mA
High Level Output Voltage	Voн	2.4			V	Iон=0, I _F =20 mA
Hysteresis (2)	HYST		10		%	
Propagation Delay, Low-High	t _{PLH}		5		μs	Vcc=5 V, I _F =20 mA
Propagation Delay, High-Low	t _{PHL}		5		μs	Vcc=5 V, I₅=20 mA
Rise Time	tr		60		ns	R _L =390 Ω, C _L =50 pF
Fall Time	t _f		15		ns	R _L =390 Ω, C _L =50 pF
COUPLED CHARACTERISTICS						
IRED Trigger Current	let				mA	Vcc=5 V
HOA2003-001				20		

- Notes

 1. It is recommended that a bypass capacitor, 0.1 µF typical, be added between V_{CC} and GND near the device in order to stabilize
- power supply line.

 2. Hysteresis is defined as the difference between the operating and release threshold intensities, expressed as a percentage of the operate threshold intensity.

ABSOLUTE MAXIMUM RATINGS SCHEMATIC (25°C Free-Air Temperature unless otherwise noted) Q Vcc Operating Temperature Range -40°C to 70°C **≨10** kΩ Voltage -40°C to 85°C Storage Temperature Range regulator Soldering Temperature (5 sec) 240°C Anode IR EMITTER -O Vo Power Dissipation 100 mW (1) Reverse Voltage 3 V Continuous Forward Current 50 mA DETECTOR 12 V (2) Supply Voltage Output Sink Current 18 mA Cathode O GND **Duration of Output** Short to V_{CC} or Ground 1.0 sec.

Honeywell reserves the right to make changes in order to improve design and supply the best products possible. Honeywell

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SWITCHING WAVEFORM

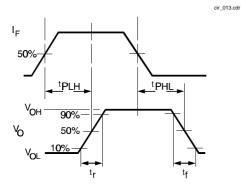
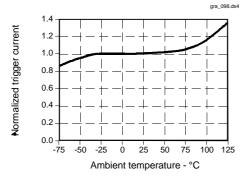


Fig. 2 IRED Trigger Current vs Temperature



All Performance Curves Show Typical Values

